

Short-wave Infrared Colloidal Quantum Dot Photodetectors on Silicon

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ABSTRACT

In this paper, two kinds of colloidal quantum dots, PbS and HgTe, are explored for SWIR photodetectors application. The colloidal dots are prepared by hot injection chemical synthesis, with organic ligands around the dots keeping them stable in solution. For the purpose of achieving efficient carrier transport between the dots in a film, these long organic ligands are replaced by shorter, inorganic ligands. We report uniform, ultra-smooth colloidal QD films without cracks realized by dip-coating and corresponding ligand exchange on a silicon substrate. Metal-free inorganic ligands, such as OH⁻ and S²⁻, are investigated to facilitate the charge carrier transport in the film. Both PbS and HgTe-based quantum dot photoconductors were fabricated on interdigitated gold electrodes. For PbS-based detectors a responsivity of 200A/W is measured at 1.5μm, due to the large internal photoconductive gain. A 2.2μm cut-off wavelength for PbS photodetectors and 2.8μm for HgTe quantum dot photodetectors are obtained.

Keywords: colloidal quantum dots, solid-state ligand exchange, photoconductor

1. INTRODUCTION

Many molecules that we want to detect in our environment have bands of absorption lines in the short-wave infrared (SWIR). Traditional high-sensitivity photodetectors used in these spectroscopic systems are discrete components based on epitaxial materials¹⁻². However, the size of these systems makes them hard to be deployed in the field. On the other hand, while the III-V semiconductor leads to the highest performance, the high material and integration cost prohibits large volume application. Low-cost MidIR photodetectors based on colloidal quantum dots (QDs) offer an alternative way to realize this functionality, either as discrete components or integrated on photonic integrated circuits³⁻⁵.

Using colloidal QDs as new photonic materials gets a lot of attention in the photonic community. The simple hot injection chemical synthesis method allows low-cost production⁶⁻⁷. By tuning the size of the QDs, the electrical and optical properties (such as the absorption cut-off wavelength) can be tuned due to the quantum size effect⁸. Furthermore, the fact that these QDs are available in solution makes it easy to do large-area heterogeneous integration on substrates, using dip coating or printing, which can offer a considerable cost reduction as compared to thermal evaporation or epitaxially grown layer stacks⁹.

Therefore, in this paper we investigate the use of two kinds of colloidal quantum dot materials, PbS and HgTe, for short-wave infrared photodetector application. We demonstrate a uniform, ultra-smooth colloidal QD film without any cracks, which is realized by dip coating and subsequent ligand exchange. Metal-free inorganic ligands, such as OH⁻ and S²⁻, are investigated to facilitate the charge carrier transport¹⁰. For PbS QD photodetectors, devices are fabricated by dip coating on prefabricated interdigitated electrodes. The HgTe QD photodetector is produced by a one step drop casting process with corresponding ligand exchange.

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2. EXPERIMENTAL SECTION

2.1 PbS QD synthesis and ligand exchange

The PbS QD synthesis is based on the procedure of Iwan Moreels *et al*^{6,8}. A stock solution of 0.16 g (5mmol) S dissolved in 15mL of oleylamine (OlAm, C18-content 80-90%) is prepared by heating the mixture under nitrogen for 30 min at 120 °C. For the synthesis, 0.834g (3 mmol) of PbCl₂ and 7.5 mL of OlAm is used in a three-neck flask. This mixture is degassed for 30 min under nitrogen at 125 °C. Afterwards the PbCl₂ solution is heated up to the required injection temperature, and then 2.25 mL of the OlAm-S stock solution (0.75 mmol of S) and 170 μL (375 μmol, half of the amount of S) of tri-n-octylphosphine (TOP) are injected into the flask. The temperature drops approximately 5-10 °C, and the resulting growth temperature is maintained throughout the reaction. After the designed growth time, the reaction is quenched by adding 10 mL of toluene and 15 mL of MeOH. After centrifugation of the suspension and decantation of the supernatant, the PbS QDs are resuspended in 10 mL of toluene. For the PbS QDs studied in this paper, the growth temperature is 160 °C and the growth time is 2 hour 30 min.

After synthesis, the PbS QDs can not be precipitated and resuspended more than once due to a loss of ligands and subsequent QDs clustering. The OlAm ligand can however easily be replaced by oleic acid (OlAc). An exchange OlAc is typically realized by adding OlAc to a toluene suspension of PbS QDs in a ratio of 1.5:10 OlAc/toluene. After precipitation with methanol (MeOH) and centrifugation, the QDs are resuspended in toluene and the exchange is repeated. Finally the QDs can be precipitated once more with MeOH to remove excess OlAc and resuspended in toluene.

In order to characterize the PbS QDs, the sizing curve developed by Iwan Moreels *et al*⁶ is used, which enables to determine the quantum dot size d (nm) directly from the spectral position of the first exciton absorption peak.

$$E_0 = 0.41 + \frac{1}{0.0252d^2 + 0.283d} \quad (1)$$

Furthermore, the QD molar extinction coefficient ϵ at 400 nm can be determined.

$$\epsilon_{400} = 0.0234d^3 \text{ cm}^{-1}/\mu\text{M} \quad (2)$$

With Beer's Law

$$A = \epsilon \cdot c_0 \cdot L \quad (L \text{ is the sample length}) \quad (3)$$

the QD concentration c_0 can be calculated directly from the absorbance at 400 nm A_{400} and QD molar extinction coefficient ϵ at 400 nm. Samples for absorbance spectroscopy are prepared by drying a known volume of the QD solution with nitrogen and resuspending them in tetrachloroethylene (C₂Cl₄).

2.2 HgTe QD synthesis and ligand exchange

Dodecanethiol-capped HgTe QDs are prepared on the procedure of Maksym V. Kovalenko *et al*⁷. Thioiglycerol stabilized HgTe QDs were synthesized in aqueous solution using the precipitation reaction of hydrogen telluride gas and mercury perchlorate. Hereafter, a phase-transfer procedure from aqueous solution to nonpolar organic solvents was carried out via the ligand exchange with dodecanethiol. In order to realize the purification, the dodecanethiol-capped HgTe QDs are resuspended in anhydrous hexane and precipitated with MeOH as solvent/non-solvent pair twice and filtering the HgTe QDs through 0.2μm PTFE filter. Finally, the HgTe QDs are resuspended in chlorobenzene.

2.3 PbS QD thin film preparation and solid state ligand exchange

The PbS QD thin film is prepared by dip coating an intrinsic Si substrate into a 1 μM PbS QDs suspension in toluene with 80 mm/min dipping speed. Afterwards, the PbS QD film is re-immersed into the metal free ligand exchange solution. After the desired ligand exchange time, formamide, acetone and isopropanol is used to remove excess exchange solution and the sample is dried under nitrogen. The dipping procedure with solid-state ligand exchange can be done repetitively to implement a multi-layer film. In order to realize solid-state ligand exchange with S²⁻ and OH⁻, 10 mg/mL Na₂S·9H₂O suspended in formamide (FA) and 0.01 mg/mL KOH in FA solution is used respectively.

2.4 Photodetector fabrication

The PbS photodetector is prepared in a way similar to the PbS thin film. The process starts with the deposition of an insulating SiO₂ layer by plasma enhanced chemical vapor deposition (PECVD). Afterwards a pair of interdigitated finger

electrodes are defined by a lift-off process, consisting of 10 nm Ni and 100 nm Au. The electrodes are designed with 2 μm wide fingers with 2 μm separation between them attached to two independent contact pads (shown in Figure 1 (a)).

The HgTe photodetector is prepared by drop casting a 0.2 μL dodecanethiol-capped HgTe suspension in chlorobenzene on a gold electrode pattern. The sample contains a pair of finger shaped gold electrodes (the pattern is defined by lithography and metal lift-off) on a glass substrate. The distance between the two fingers is 15 μm and the active area of the detector is 15 μm * 8 mm (shown in Figure 1(b)). For the purpose of solid-state ligand exchange, 0.01 mg/mL KOH in FA solution is directly dropped on the film for 10 seconds and afterwards rinsed with the same recipe for PbS ligand exchange.

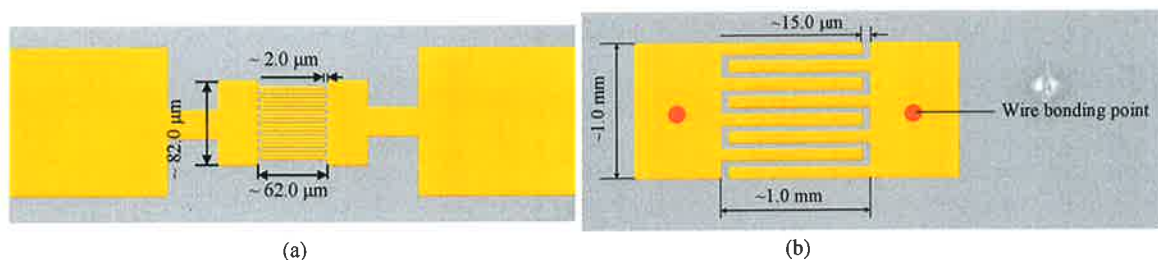


Figure 1. Illustration of (a) PbS and (b) HgTe detector electrodes design (top view)

3. RESULTS AND DISCUSSION

3.1 PbS QD synthesis

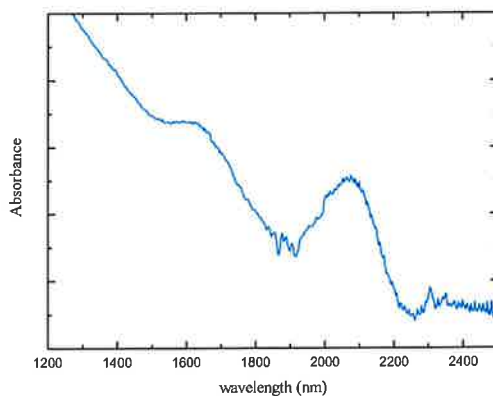


Figure 2. Absorbance spectra of PbS QD suspensions in the short-wave infrared, synthesized at 160 $^{\circ}\text{C}$ with a total growth time of 2 hour 30 min.

Figure 2 shows a typical absorbance spectrum with a first exciton transition peak in the short-wave infrared range, illustrating a cut-off wavelength of 2.2 μm . The quantum dot size is about 10 nm according to the sizing curve. According to Beer's Law, the concentration is about 2.106 $\mu\text{Mol/L}$.

3.2 Solid state ligand exchange of PbS QD film

According to the absorbance spectra, PbS QDs can be used to achieve interband transitions up to 2.2 μm . Thus we can realize photodetectors based on such colloidal QDs on silicon or on silicon waveguide circuits with solution-based processes, e.g. drop casting, spin coating, printing, etc. Nevertheless, the electrically insulating organic ligand shells existing in the as-deposited QD film prohibits charge carrier transport in the film and therefore they need to be removed to obtain photoconductive devices. For this purpose, a solid-state metal free ligand exchange process is used to remove the organic surrounding QDs. An FTIR is used to monitor the effect of ligand exchange treatments.

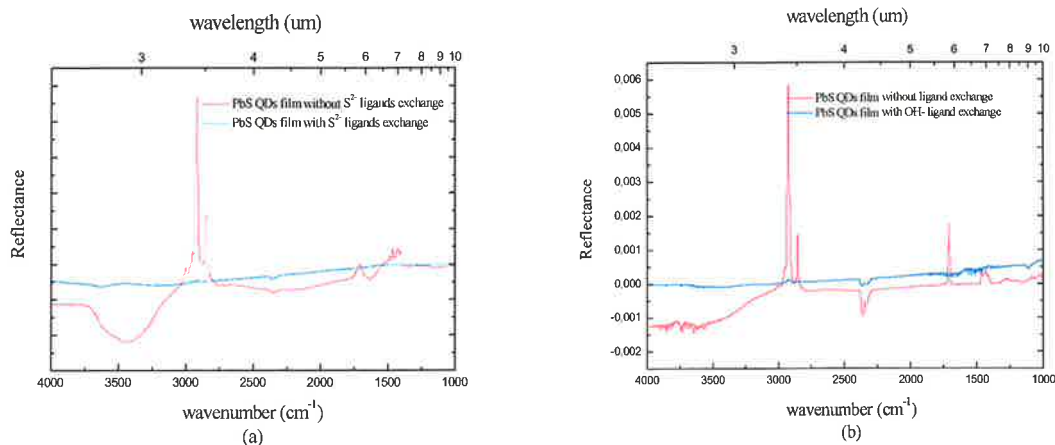


Figure 3. (a) Reflection- Fourier Transform InfraRed (FTIR) spectra of OlAc-capped PbS colloidal QD film and S^{2-} -capped PbS colloidal QD film after $Na_2S \cdot 9H_2O$ treatment. (b) Reflection-FTIR spectra of OlAc-capped PbS colloidal QD film and OH^- -capped PbS colloidal QD film after KOH treatment.

Figure 3 (a) compares the reflection-FTIR spectra of OlAc-capped PbS colloidal QD film and S^{2-} -capped PbS colloidal QD film after $Na_2S \cdot 9H_2O$ treatment. After the treatment, the $C = C$ stretching peak around 3010 cm^{-1} , $-CH_2$ asymmetric stretching at 2920 cm^{-1} and $-CH_3$ symmetric stretching at 2850 cm^{-1} no longer exists, which indicates that most of the organic ligands are removed. Figure 3 (b) shows similar results for KOH treatment, showing also that most of the organics are removed from the QD film.

The ligand exchange induces a clustering of the nanoparticles due to the removal of the long ligands. This is a main challenge that needs to be addressed, since resulting cracks in the QD film will prevent charge carrier transport. In this paper, multiple times dip coating with solid state ligand exchange is used to overcome this issue.

Figure 4 (a), (b), (c) show the surface morphology of a PbS QD film deposited by of 6 time dipping without chemical treatment, with $Na_2S \cdot 9H_2O$ treatment and KOH treatment, respectively. After chemical treatment, Figure 4 (b) and (c) reveal clearly a reduction of interparticle spacing, which results in a mobility increase of the film. Specifically, compared with KOH treatment, the $Na_2S \cdot 9H_2O$ treated film exhibits more close packaging of the QDs. This corresponds well with the optoelectronic characterization results, as will be discussed later. Moreover, the film morphology after treatment illustrates that a crack-free and homogenous film can be implemented, which is suitable for optoelectronic applications.



Figure 4. Scanning electron microscope (SEM) images of (a) OlAc-capped PbS colloidal QD film (b) S^{2-} -capped PbS colloidal QD film (c) OH^- -capped PbS colloidal QD film.

3.3 PbS Photodetector characterization

The current-voltage characteristics of PbS photoconductive photodetectors is done by surface illumination with a fiber coupled near infrared SLED ($\lambda \sim 1.55 \mu\text{m}$). Figure 5 presents the I-V characteristics as a function of incident optical power. Under illumination, the resistance of S^{2-} capped PbS QD photodetector increases from a dark resistivity of $2.67 \text{ k}\Omega$ to $1.22 \text{ k}\Omega$ at 10 V bias under 16 mW optical illumination; the OH^- capped PbS photodetector shows a similar trend from dark resistivity of $7.35 \text{ k}\Omega$ to $1.57 \text{ k}\Omega$ under the same illuminate condition. The OH^- capped PbS colloidal QD detector shows a lower conductivity compared to S^{2-} capped PbS QD detector, which corresponds to the more close packing of S^{2-} capped PbS QDs after ligand exchange.

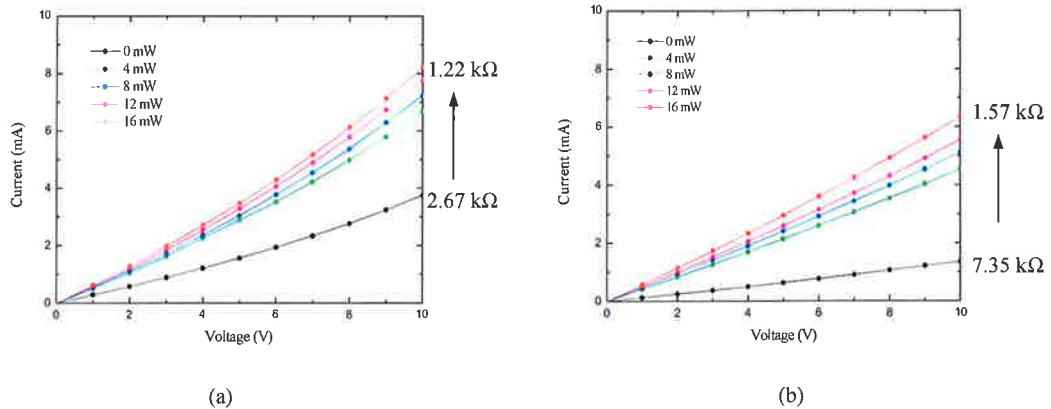


Figure 5. Current-voltage characteristics of processed (a) S^{2-} capped PbS (b) OH^- capped PbS colloidal QD photoconductive photodetectors.

Figure 6 shows the responsivity of OH^- capped PbS QD detector as a function of illumination power level. The curve exhibits an increase of responsivity with decreasing illumination. For 500 nW illumination power with 10 V bias, the responsivity can reach more than 200 A/W . This rather high value implies a high internal photoconductive gain, which is due to the long carrier lifetime compare to the carrier transit time. These long lifetime carrier result from the trap states inside the QD thin film. With the increase of illumination power, the long-lived trap states will be filled and consequently a lower gain will result.

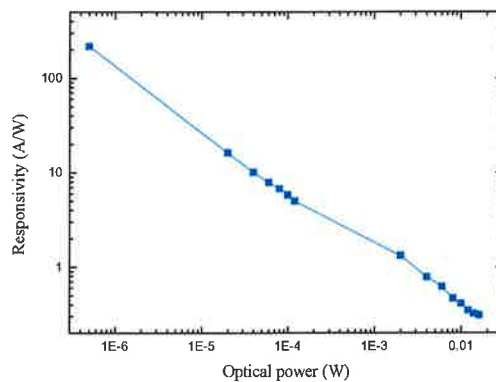


Figure 6. Responsivity dependence as a function of optical power at $1.55 \mu\text{m}$ and a bias voltage of 10 V for an OH^- capped PbS colloidal QD photodetector.

FTIR-based calibration measurements are used to get the spectral response of the PbS photodetector¹¹. An internal tungsten halogen source in the FTIR spectrometer is modulated by a Michelson interferometer and is used to illuminate the photodetector with a set of gold mirrors. The photoconductor is driven by 0.3 mA current and the resultant voltage drop signal is sent back to the FTIR electrical input to calculate the spectral dependence of the responsivity (in arbitrary units). The normalized detector responsivities as a function of wavelength for PbS QD photodetector is presented in Figure 7. The two spectral response curves illustrate that the first transition peak of PbS QDs (around 2.0 μm) still exists after ligand exchange, and photodetection up to 2.2 μm can be achieved.

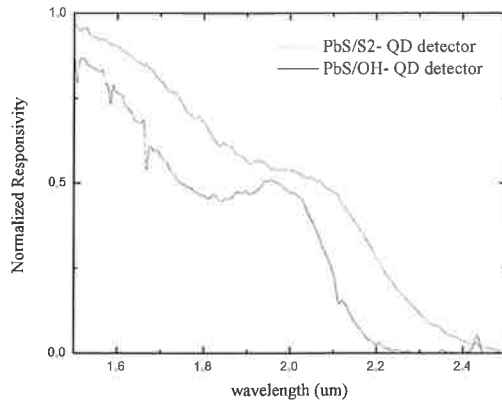


Figure 7. Normalized detector responsivity as a function of wavelength for S²⁻ capped and OH⁻ capped PbS QD photodetector.

3.4 HgTe Photodetector characterization

For the HgTe photodetector, an incandescent light / monochromator combination is used to acquire current-voltage characteristics and spectral response curve. The normalized current-voltage characteristics of the HgTe photodetector can be seen in Figure 8, in order to compare HgTe photodetectors and PbS devices. The PbS contrast sample is prepared by drop casting 0.2 μL OlAc-capped PbS suspended in toluene on a gold electrode pattern, after which 0.01 mg/mL KOH in FA solution is drop casted on the film for 10 seconds ligand exchange, after which the sample is rinsed to remove excess KOH.

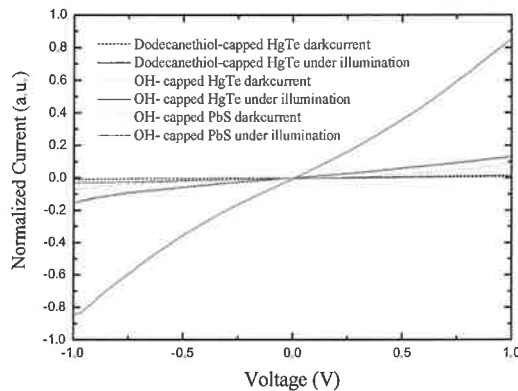


Figure 8. Current-voltage characteristics of processed HgTe and PbS photoconductive detectors.

The graph illustrates that the HgTe colloidal quantum dots exhibit much higher photosensitivity compared to PbS. Also, the measurements show that OH- capped HgTe QDs outperform dodecanethiol-capped HgTe QDs, which is most likely related to the shorter ligand length in the first case.

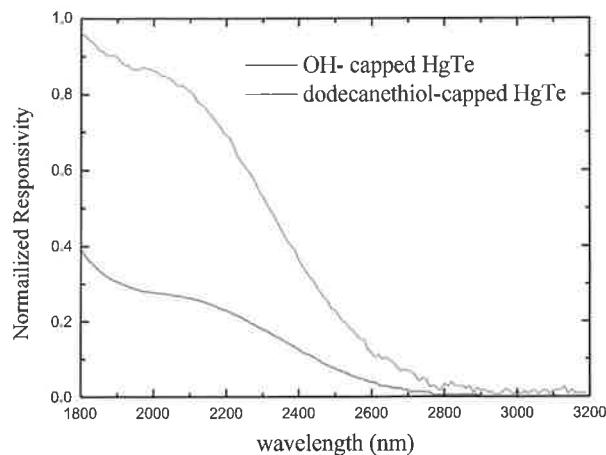


Figure 9. normalized spectral response of dodecanethiol-capped and OH- capped HgTe QD photoconductive photodetectors.

The normalized spectral response curves of HgTe photodetector is presented in Figure 9. Both curves illustrate that HgTe detectors are useful for near-infrared and mid-infrared photodetection. The higher responsivity of OH- capped HgTe QD detector reveals that metal-free ligand exchange method is promising to improve the detector performance.

4. CONCLUSIONS

In this paper, two kinds of colloidal quantum dot material, PbS and HgTe, are explored for SWIR photodetector applications. We have demonstrated a uniform, ultra-smooth colloidal QD film without cracks by dip coating and subsequent ligand exchange. Metal-free inorganic ligands, such as OH- and S²⁻ are investigated to facilitate the charge carrier transport. PbS photoconductors with a responsivity of 200A/W are obtained at 1.5 μ m (cut-off wavelength 2.2 μ m). We also show that HgTe photodetectors with a cut-off wavelength of 2.8 μ m can be realized by metal free ligand exchange, with improved performance compared to PbS detectors. The integration of these photodetectors on silicon waveguide circuits will be discussed during the conference.

ACKNOWLEDGEMENT

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Quantum Sensing and Nanophotonic Devices X
Manijeh Razeghi
San Francisco, California, USA | February 02, 2013

Abstract | References

abstract

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Topics

Chemicals ; Coating ; Electrodes ; Gold ; Metals ; Photodetectors ; Photoresistors ; Quantum dots ; Sensors ; Short wave infrared radiation

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 Montpellier 2 (France) [8631-72]

**Applications of active plasmonic devices (Invited
 Paper)**, Institut Langevin (France) [8631-36]
 Wed 12:20 pm to 2:00 pm

SESSION 14

Room: 122 (Exhibit Level) Wed 2:00 pm to 3:10 pm

Nanophotonics

Session Chairs: **Jingyu Lin**, Texas Tech Univ. (USA); **Woo-Gwang Jung**, Kookmin Univ. (Korea, Republic of)

2:00 pm: Infrared spectral filters based on guided-mode resonance with subwavelength structures (Invited Paper), Emilie Sakat, Grégory Vincent, ONERA (France); Petru Ghenuche, Nathalie Bardou, Stéphane Collin, Fabrice Pardo, Jean-Luc Pelouard, Lab. de Photonique et de Nanostructures (France); Riad Haïdar, ONERA (France) [8631-74]

2:20 pm: Ultrastrong optical modulation in waveguides by conducting interfaces, Farhad Karimi, Sharif Univ. of Technology (Iran, Islamic Republic of); Sina Khorasani, Georgia Institute of Technology (USA) [8631-75]

2:35 pm: Fabrication of high-quality large-area plasmonic oligomers by angle-controlled colloidal nanolithography, Jun Zhao, Univ. Stuttgart (Germany); Sven Burger, Konrad-Zuse-Zentrum für Informationstechnik Berlin (Germany); Bettina Frank, Harald Giessen, Univ. Stuttgart (Germany) .. [8631-76]

2:50 pm: Nanostructured photonic and plasmonic materials for enhanced resonant light absorption (Invited Paper), Koray Aydin, Northwestern Univ. (USA) [8631-103]

Coffee Break Wed 3:10 pm to 3:40 pm

SESSION 15

Room: 122 (Exhibit Level) Wed 3:40 pm to 5:10 pm

Nanomaterials II

Session Chairs: **Grzegorz Sek**, Wroclaw Univ. of Technology (Poland); **Ferechteh Hosseini Teherani**, Novation (France)

3:40 pm: Structural and optical properties of (In,Ga)As/GaP quantum dots and (GaAsPN/GaPN) diluted-nitride nanolayers coherently grown onto GaP and Si substrates for photonics and photovoltaics applications (Invited Paper), Olivier Durand, Cédric Robert, Institut National des Sciences Appliquées de Rennes (France); Tra Nguyen Thanh, Samy Almosni, Institut National des Sciences Appliquées de Rennes (France); Thomas Quinci, Institut National des Sciences Appliquées de Rennes (France) and Institut National de l'Energie Solaire (France); Jitesh Kuyyail, Institut National des Sciences Appliquées de Rennes (France); Charles Cornet, Antoine Létoublon, Institut National des Sciences Appliquées de Rennes (France); Christophe Levallois, Jean-Marc Jancu, Jacky Even, Laurent Pédesseau, Mathieu Perrin, Nicolas Bertru, A. Sakri, Institut National des Sciences Appliquées de Rennes (France); Nathalie Boudet, G2Elab (France); Anne Ponchet, Ctr. d'Elaboration de Matériaux et d'Etudes Structurales (France); P. Rale, Ecole Nationale Supérieure de Chimie de Paris (France); Laurent Lombez, Jean-Francois Guillemoles, Institut de Recherche et Développement sur l'Energie Photovoltaïque (France); Xavier Marie, Institut National des Sciences Appliquées de Toulouse (France); A. Balocchi, Univ. de Toulouse (France); P. Turban, Sylvain Tricot, Institut de Physique de Rennes (France); Mircea Modreanu, Tyndall National Institute-University College Cork, Lee Maltings, Prospect Row (Ireland); Slimane Loualiche, Alain Le Corre, Institut National des Sciences Appliquées de Rennes (France) [8631-78]

4:00 pm: Short-wave infrared colloidal quantum dot photodetectors on silicon, Chen Hu, Alban A. Gassenq, Yolanda Justo, Univ. Gent (Belgium); Sergii Yakunin, Wolfgang Heiss, Johannes Kepler Univ. Linz (Austria); Zeger Hens, Gunther Roelkens, Univ. Gent (Belgium) [8631-79]

4:15 pm: Optoelectronic properties of hexagonal boron nitride epilayers (Invited Paper), X. K. Cao, Texas Tech Univ. (USA); S. Majety, J. Li, Jingyu Lin, Hongxing Jiang, Texas Tech Univ. (USA) [8631-80]

4:35 pm: Thermal conductivity tensor of semiconductor layers using two-wire 3-omega method, Chuanle Zhou, Northwestern Univ. (USA); Gregor Koblmüller, Max Bichler, Gerhard Abstreiter, Walter Schottky Institut (Germany); Matthew Grayson, Northwestern Univ. (USA) [8631-94]

4:50 pm: Transport properties related to spin-orbit interaction (Invited Paper), Henri-Jean Drouhin, Ecole Polytechnique (France); Federico Bottegoni, Ecole Polytechnique (France) and Politecnico di Milano (Italy); Alberto Ferrari, Politecnico di Milano (Italy); Hoai T. Nguyen, Vietnamese Academy of Science and Technology (Viet Nam); Jean-Eric Wegrowe, Ecole Polytechnique (France); Guy Fishman, Univ. Paris-Sud 11 (France) [8631-73]

POSTERS-WEDNESDAY

Room: 103 (Exhibit Level) Wed 6:00 pm to 8:00 pm

Conference attendees are invited to attend the OPTO poster session on Wednesday evening. Come view the posters, enjoy light refreshments, ask questions, and network with colleagues in your field. Authors of poster papers will be present to answer questions concerning their papers. Attendees are required to wear their conference registration badges to the poster sessions. Poster authors, view poster presentation guidelines and set-up instructions at <http://spie.org/PWPosterGuidelines>.

Investigation of temperature dependence on heterojunction bipolar light-emitting transistors embedded InGaAs/GaAs quantum wells, Tzu-hsuan Huang, Heng-Jui Chang, Kuo-Min Huang, Shao-Yen Chiu, Yueh-Lin Lee, National Tsing Hua Univ. (Taiwan); Wei-Jiun Hong, National Tsing Hua University (Taiwan); Chong-Long Ho, Meng-Chyi Wu, National Tsing Hua Univ. (Taiwan) [8631-90]

Nanostructured enhanced chemical sensing surfaces for mid-IR molecular absorption, Andrea Dunbar, Ctr. Suisse d'Electronique et de Microtechnique SA (Switzerland); Edward Threlfall, Photon Design (United Kingdom); Rolf Eckert, Ctr. Suisse d'Electronique et de Microtechnique SA (Switzerland); Silvia Angeloni, CSEM SA (Switzerland); Ross P. Stanley, Ctr. Suisse d'Electronique et de Microtechnique SA (Switzerland) [8631-91]

The response properties of NbN superconductor nanowire for multi-photon, Lin Kang, Yu Zhou, Labao Zhang, Pei-Heng Wu, Nanjing Univ. (China) [8631-92]

High-speed InGaAs/InP single-photon avalanche photodiode with tunable gating frequency, Yixin Zhang, Xuping Zhang, Shun Wang, Nanjing Univ. (China) [8631-96]

Thursday 7 February

KEYNOTE SESSION

Room: 122 (Exhibit Level) 8:00 am to 8:30 am

Session Chair: **Manijeh Razeghi**, Northwestern Univ. (USA)

8:00 am: Advanced PV technologies: challenges and opportunities (Keynote Presentation), Devendra K. Sadana, IBM Thomas J. Watson Research Ctr. (USA) [8631-77]

SESSION 16

Room: 122 (Exhibit Level) Thu 8:30 am to 10:00 am

THz and Infrared Technology

Session Chairs: **Can Bayram**, IBM Thomas J. Watson Research Ctr. (USA); **Emmanuel Rosencher**, ONERA (France), Ecole Polytechnique (France)

8:30 am: Quantum-dot micropillars for parametric THz emission (Invited Paper), Silvia Mariani, Alessio Andronico, Ivan Favero, Sara Ducci, Yanko Todorov, Carlo Sirtori, Univ. Paris 7-Denis Diderot (France); Martin Kamp, Julius-Maximilians-Univ. Würzburg (Germany); Julien Claudon, Jean-Michel Gérard, Univ. Joseph Fourier (France) and Commissariat à l'Energie Atomique (France); Tianwu Wang, Peter U. Jepsen, Technical Univ. of Denmark (Denmark); Giuseppe Leo, Univ. Paris 7-Denis Diderot (France) [8631-81]

8:50 am: Electronic temperature in phonon-photon-phonon terahertz quantum cascade devices with high-operating temperature performance, Gaetano Scamarcio, Pietro Patimisco, Maria V. Santacroce, Pasquale Tempesta, Univ. degli Studi di Bari (Italy); Vincenzo Spagnolo, Politecnico di Bari (Italy); Miriam S. Vitiello, Lab. NEST (Italy) and Scuola Normale Superiore di Pisa (Italy); Emmanuel Dupont, Saead Fatholouloumi, Sylvain R. Laframboise, National Research Council Canada (Canada); Seyed G. Razavipour, Zbigniew Wasilewski, Dayan Ban, Univ. of Waterloo (Canada); H. C. Liu, Shanghai Jiao Tong Univ. (China) [8631-82]

9:05 am: Far-infrared InAs/AlSb quantum cascade lasers (Invited Paper), Roland Teissier, Michael Bahrz, Guillaume Lollia, Alexei N. Baranov, Univ. Montpellier 2 (France); Adel Bousseksou, Raffaele Colombelli, Univ. Paris-Sud 11 (France) [8631-83]

9:25 am: Room-temperature nanowire terahertz photodetectors (Invited Paper), Lorenzo Romeo, Scuola Normale Superiore di Pisa (Italy); Dominique Coquillat, Univ. Montpellier 2 (France); Leonardo Viti, Daniele Ercolani, Lucia Sorba, Scuola Normale Superiore di Pisa (Italy); Wojciech Knap, Univ. Montpellier 2 (France); Alessandro Tredicucci, Lab. NEST (Italy); Miriam S. Vitiello, Studi di Roma La Sapienza (Italy) [8631-84]